General Purpose Transistors

NPN Silicon

BC818-40L, NSVBC818-40L

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	25	V
Collector – Base Voltage	V _{CBO}	30	V
Emitter – Base Voltage	V _{EBO}	5.0	V
Collector Current – Continuous	Ι _C	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

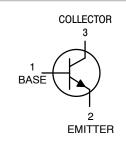
1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = 0.4 x 0.3 x 0.024 in 99.5% alumina.



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MARKING DIAGRAMS



6G = Specific Device Code

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location) *Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
BC818-40LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
NSVBC818-40LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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BC818-40L, NSVBC818-40L

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

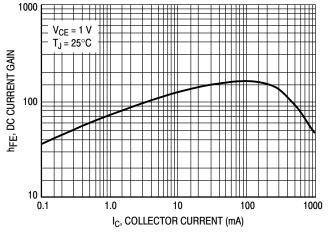
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•				
Collector – Emitter Breakdown Voltage (I _C = 10 mA)	V _{(BR)CEO}	25	_	_	V
Collector – Emitter Breakdown Voltage (V _{EB} = 0, I_C = 10 μ A)	V _(BR) CES	30	_	_	V
Emitter – Base Breakdown Voltage (I _E = 1.0 μA)	V _{(BR)EBO}	5.0	_	_	V
Collector Cutoff Current $(V_{CB} = 20 \text{ V})$ $(V_{CB} = 20 \text{ V}, \text{ T}_{\text{A}} = 150^{\circ}\text{C})$	I _{CBO}			100 5.0	nA μA
ON CHARACTERISTICS					
DC Current Gain (I _C = 100 mA, V _{CF} = 1.0 V)	h _{FE}	250	_	600	-

$(I_{C} = 100 \text{ mA}, V_{CE} = 1.0 \text{ V})$ $(I_{C} = 500 \text{ mA}, V_{CE} = 1.0 \text{ V})$		250 40	-	- 600	
Collector – Emitter Saturation Voltage $(I_C = 500 \text{ mA}, I_B = 50 \text{ mA})$	V _{CE(sat)}	-	-	0.7	V
Base – Emitter On Voltage (I _C = 500 mA, V _{CE} = 1.0 V)	V _{BE(on)}	-	-	1.2	V

SMALL-SIGNAL CHARACTERISTICS

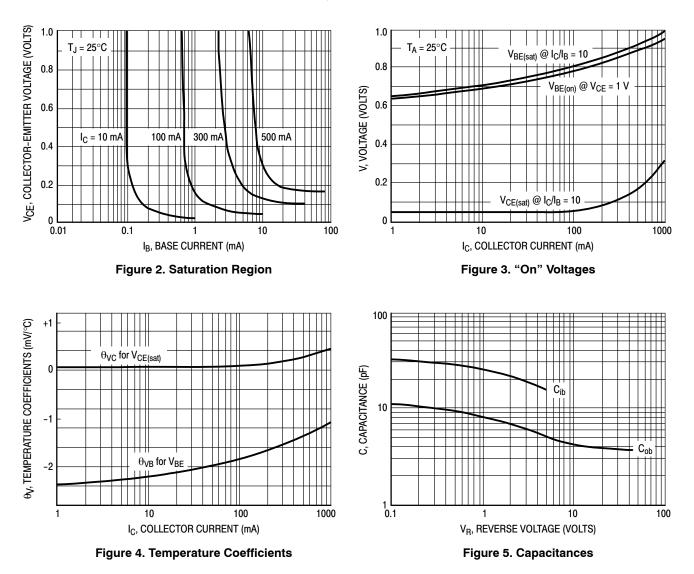
Current – Gain – Bandwidth Product ($I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ Vdc}, f = 100 \text{ MHz}$)	f _T	100	-	-	MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)	C _{obo}	-	10	-	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.





BC818-40L, NSVBC818-40L



MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

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TOP VIEW

SIDE VIEW

Нe

DETAIL A

-3X b

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SCALE 4:1

A____ ' A1SOT-23 (TO-236) CASE 318 ISSUE AT

0.25

-1.1

DETAIL A

END VIEW

DATE 01 MAR 2023

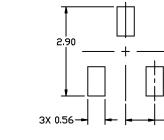
3X -0.95

0.95

NDTES

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
с	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
Η _E	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10*	0*		10*



PITCH RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

M = Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

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SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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